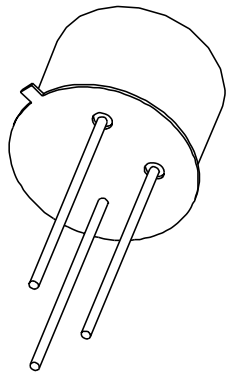


DATA SHEET



2N2219; 2N2219A **NPN switching transistors**

Product specification
Supersedes data of 1997 May 07
File under Discrete Semiconductors, SC04

1997 Sep 03

NPN switching transistors

2N2219; 2N2219A

FEATURES

- High current (max. 800 mA)
- Low voltage (max. 40 V).

APPLICATIONS

- High-speed switching
- DC and VHF/UHF amplification, for 2N2219 only.

DESCRIPTION

NPN switching transistor in a TO-39 metal package.
PNP complement: 2N2905 and 2N2905A.

PINNING

| PIN | DESCRIPTION |
|-----|------------------------------|
| 1 | emitter |
| 2 | base |
| 3 | collector, connected to case |

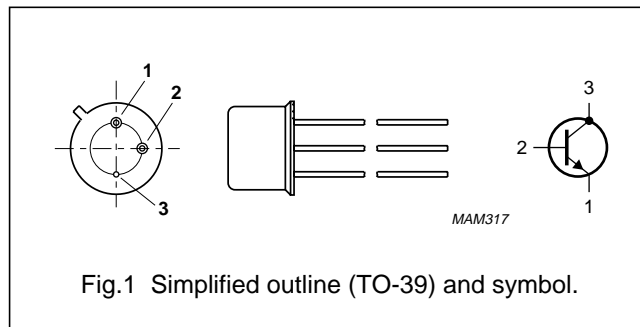


Fig.1 Simplified outline (TO-39) and symbol.

QUICK REFERENCE DATA

| SYMBOL | PARAMETER | CONDITIONS | MIN. | MAX. | UNIT |
|------------------|---------------------------|---|------|------|------|
| V _{CBO} | collector-base voltage | open emitter | | | |
| | 2N2219 | | – | 60 | V |
| | 2N2219A | | – | 75 | V |
| V _{CEO} | collector-emitter voltage | open base | | | |
| | 2N2219 | | – | 30 | V |
| | 2N2219A | | – | 40 | V |
| I _C | collector current (DC) | | – | 800 | mA |
| P _{tot} | total power dissipation | T _{amb} ≤ 25 °C | – | 800 | mW |
| h _{FE} | DC current gain | I _C = 10 mA; V _{CE} = 10 V | 75 | – | |
| f _T | transition frequency | I _C = 20 mA; V _{CE} = 20 V; f = 100 MHz | | | |
| | 2N2219 | | 250 | – | MHz |
| | 2N2219A | | 300 | – | MHz |
| t _{off} | turn-off time | I _{Con} = 150 mA; I _{Bon} = 15 mA; I _{Boff} = –15 mA | – | 250 | ns |

NPN switching transistors

2N2219; 2N2219A

LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 134).

| SYMBOL | PARAMETER | CONDITIONS | MIN. | MAX. | UNIT |
|------------------|-------------------------------|------------------------------------|------|------|------|
| V _{CBO} | collector-base voltage | open emitter | | | |
| | 2N2219 | | – | 60 | V |
| | 2N2219A | | – | 75 | V |
| V _{CEO} | collector-emitter voltage | open base | | | |
| | 2N2219 | | – | 30 | V |
| | 2N2219A | open base; I _C ≤ 500 mA | – | 40 | V |
| V _{EBO} | emitter-base voltage | open collector | | | |
| | 2N2219 | | – | 5 | V |
| | 2N2219A | | – | 6 | V |
| I _C | collector current (DC) | | – | 800 | mA |
| I _{CM} | peak collector current | | – | 800 | mA |
| I _{BM} | peak base current | | – | 200 | mA |
| P _{tot} | total power dissipation | T _{amb} ≤ 25 °C | – | 800 | mW |
| | | T _{case} ≤ 25 °C | – | 3 | W |
| T _{stg} | storage temperature | | –65 | +150 | °C |
| T _j | junction temperature | | – | 200 | °C |
| T _{amb} | operating ambient temperature | | –65 | +150 | °C |

THERMAL CHARACTERISTICS

| SYMBOL | PARAMETER | CONDITIONS | VALUE | UNIT |
|---------------------|---|-------------|-------|------|
| R _{th j-a} | thermal resistance from junction to ambient | in free air | 190 | K/W |
| R _{th j-c} | thermal resistance from junction to case | | 50 | K/W |

NPN switching transistors

2N2219; 2N2219A

CHARACTERISTICS

$T_j = 25\text{ }^\circ\text{C}$ unless otherwise specified.

| SYMBOL | PARAMETER | CONDITIONS | MIN. | MAX. | UNIT |
|-------------|---|--|------|------|---------------|
| I_{CBO} | collector cut-off current 2N2219 | $I_E = 0; V_{CB} = 50\text{ V}$ | – | 10 | nA |
| | | $I_E = 0; V_{CB} = 50\text{ V}; T_{amb} = 150\text{ }^\circ\text{C}$ | – | 10 | μA |
| I_{CBO} | collector cut-off current 2N2219A | $I_E = 0; V_{CB} = 60\text{ V}$ | – | 10 | nA |
| | | $I_E = 0; V_{CB} = 60\text{ V}; T_{amb} = 150\text{ }^\circ\text{C}$ | – | 10 | μA |
| I_{EBO} | emitter cut-off current | $I_C = 0; V_{EB} = 3\text{ V}$ | – | 10 | nA |
| h_{FE} | DC current gain | $I_C = 0.1\text{ mA}; V_{CE} = 10\text{ V}$ | 35 | – | |
| h_{FE} | DC current gain | $I_C = 1\text{ mA}; V_{CE} = 10\text{ V}$ | 50 | – | |
| h_{FE} | DC current gain | $I_C = 10\text{ mA}; V_{CE} = 10\text{ V}$ | 75 | – | |
| h_{FE} | DC current gain 2N2219A | $I_C = 10\text{ mA}; V_{CE} = 10\text{ V}; T_{amb} = -55\text{ }^\circ\text{C}$ | 35 | – | |
| h_{FE} | DC current gain | $I_C = 150\text{ mA}; V_{CE} = 1\text{ V}; \text{note 1}$ | 50 | – | |
| h_{FE} | DC current gain | $I_C = 150\text{ mA}; V_{CE} = 10\text{ V}; \text{note 1}$ | 100 | 300 | |
| h_{FE} | DC current gain 2N2219 2N2219A | $I_C = 500\text{ mA}; V_{CE} = 10\text{ V}; \text{note 1}$ | 30 | – | |
| | | | 40 | – | |
| V_{CEsat} | collector-emitter saturation voltage 2N2219 2N2219A | $I_C = 150\text{ mA}; I_B = 15\text{ mA}; \text{note 1}$ | – | 400 | mV |
| | | | – | 300 | mV |
| V_{CEsat} | collector-emitter saturation voltage 2N2219 2N2219A | $I_C = 500\text{ mA}; I_B = 50\text{ mA}; \text{note 1}$ | – | 1.6 | V |
| | | | – | 1 | V |
| V_{BEsat} | base-emitter saturation voltage 2N2219 2N2219A | $I_C = 150\text{ mA}; I_B = 15\text{ mA}; \text{note 1}$ | – | 1.3 | V |
| | | | 0.6 | 1.2 | V |
| V_{BEsat} | base-emitter saturation voltage 2N2219 2N2219A | $I_C = 500\text{ mA}; I_B = 50\text{ mA}; \text{note 1}$ | – | 2.6 | V |
| | | | – | 2 | V |
| C_c | collector capacitance | $I_E = I_e = 0; V_{CB} = 10\text{ V}$ | – | 8 | pF |
| C_e | emitter capacitance 2N2219A | $I_C = I_c = 0; V_{EB} = 500\text{ mV}$ | – | 25 | pF |
| f_T | transition frequency 2N2219 2N2219A | $I_C = 20\text{ mA}; V_{CE} = 20\text{ V}; f = 100\text{ MHz};$ | 250 | – | MHz |
| | | | 300 | – | MHz |
| F | noise figure 2N2219A | $I_C = 0.2\text{ mA}; V_{CE} = 5\text{ V}; R_S = 2\text{ k}\Omega;$ $f = 1\text{ kHz}; B = 200\text{ Hz}$ | – | 4 | dB |

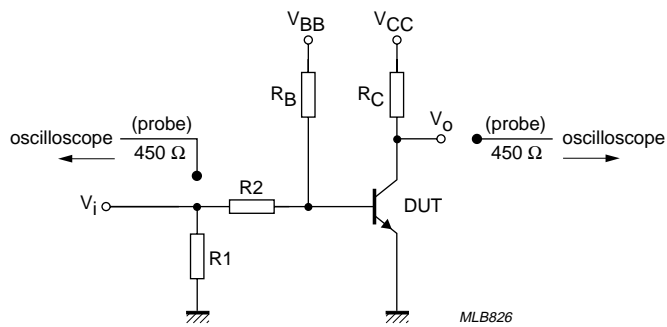
NPN switching transistors

2N2219; 2N2219A

| SYMBOL | PARAMETER | CONDITIONS | MIN. | MAX. | UNIT |
|---|---------------|---|------|------|------|
| Switching times (between 10% and 90% levels) for type 2N2219A; see Fig.2 | | | | | |
| t_{on} | turn-on time | $I_{Con} = 150 \text{ mA}; I_{Bon} = 15 \text{ mA};$ $I_{Boff} = -15 \text{ mA}$ | – | 35 | ns |
| t_d | delay time | | – | 15 | ns |
| t_r | rise time | | – | 20 | ns |
| t_{off} | turn-off time | | – | 250 | ns |
| t_s | storage time | | – | 200 | ns |
| t_f | fall time | | – | 60 | ns |

Note

1. Pulse test: $t_p \leq 300 \mu\text{s}; \delta \leq 0.02$.



$V_i = 9.5 \text{ V}; T = 500 \mu\text{s}; t_p = 10 \mu\text{s}; t_r = t_f \leq 3 \text{ ns}.$
 $R_1 = 68 \Omega; R_2 = 325 \Omega; R_B = 325 \Omega; R_C = 160 \Omega.$
 $V_{BB} = -3.5 \text{ V}; V_{CC} = 29.5 \text{ V}.$
 Oscilloscope: input impedance $Z_i = 50 \Omega.$

Fig.2 Test circuit for switching times.

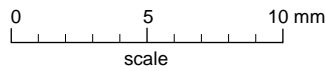
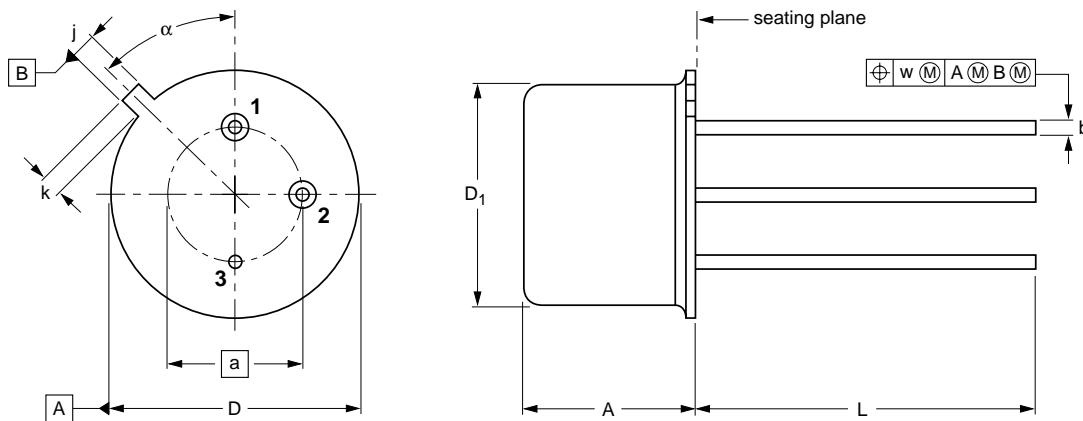
NPN switching transistors

2N2219; 2N2219A

PACKAGE OUTLINE

Metal-can cylindrical single-ended package; 3 leads

SOT5/11



DIMENSIONS (mm are the original dimensions)

| UNIT | A | a | b | D | D ₁ | j | k | L | w | α |
|------|--------------|------|--------------|--------------|----------------|--------------|--------------|--------------|-----|-----|
| mm | 6.60 6.35 | 5.08 | 0.48 0.41 | 9.39 9.08 | 8.33 8.18 | 0.85 0.75 | 0.95 0.75 | 14.2 12.7 | 0.2 | 45° |

| OUTLINE VERSION | REFERENCES | | | | EUROPEAN PROJECTION | ISSUE DATE |
|-----------------|------------|-------|------|--|---------------------|------------|
| | IEC | JEDEC | EIAJ | | | |
| SOT5/11 | | TO-39 | | | | 97-04-11 |

NPN switching transistors

2N2219; 2N2219A

DEFINITIONS

| | |
|---|---|
| Data sheet status | |
| Objective specification | This data sheet contains target or goal specifications for product development. |
| Preliminary specification | This data sheet contains preliminary data; supplementary data may be published later. |
| Product specification | This data sheet contains final product specifications. |
| Limiting values | |
| Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability. | |
| Application information | |
| Where application information is given, it is advisory and does not form part of the specification. | |

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